



Bidirectional ESD protection Diode with normal capacitance

General Description

The LESD11LL5.0C is designed to protect voltage sensitive components from damage or latch-up due to ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD for board level. Because of its small size and bi-directional design, it is ideal for use in cellular phones, and portable applications that require audio line protection.

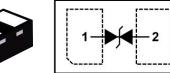
Specification Features

- Miniaturized packaging size suitable for high-density applications: nom 0.024" x 0.012" (0.6x0.3 mm)
- Standard Capacitance 19 pF
- Low Clamping Voltage:V_C=11V@I_{PP}=8.0A
- Reverse Working (Stand-off) Voltage: 5.0V
- Low Leakage current
- Response Time is Typically < 1 ns

Application

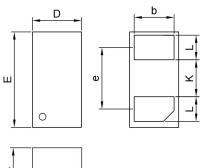
- Smartphones, tablet computers
- Blu-ray and DVD recorders and players
- Video equipment and accessories





DFN0603-2L

Schematic Diagram





DFN0603-2L

	М	illimete	ers	Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
	(mm)	(mm)	(mm)	(mm)	(mm)	(mm)	
Α	0.30	0.32	0.35	0.0106	0.0125	0.0137	
b	0.22	0.22	0.26	0.0086	0.0086	0.0102	
D	0.27	0.30	0.33	0.0106	0.0118	0.0129	
е	0.40BSC			0.0157BSC			
E	0.57	0.60	0.63	0.0224	0.0236	0.0248	
L	0.14	0.16	0.18	0.0055	0.0062	0.0070	
K	0.20	0.24	0.25	0.0078	0.0094	0.0098	

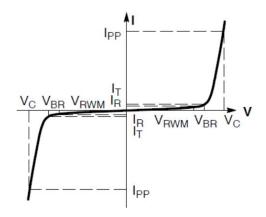
Absolute Maximum Rating

Rating	Symbol	Value	Unit
Peak pulse power (tp = 8/20µs)	P _{PK}	88	W
ESD according to IEC61000-4-2 air discharge		±30	
ESD according to IEC61000-4-2 contact discharge	V_{ESD}	±30	kV
Operating Temperature Range	TJ	-40~85	$^{\circ}$
Storage temperature	T _{STG}	-55~150	$^{\circ}$

LESD11LL5.0C

Characteristics(T_J =25℃ unless otherwise specified)

Symbol	Parameter		
I _{PP}	Maximum Reverse Peak Pulse Current		
Vc	Clamping Voltage @ I _{PP}		
V _{RWM}	Working Peak Reverse Voltage		
I _R	Maximum Reverse Leakage Current @ V _{RWM}		
I _T	Test Current		
V_{BR}	Breakdown Voltage @ I _T		
P _{PK}	Peak Power Dissipation		
С	Max. Capacitance @ V_R = 0 and freq.=1 MHz		



Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Reverse Stand-off Voltage	V _{RWM}				5.0	V
Reverse Breakdown Voltage	V_{BR}	I _T =1mA	5.6		8.0	V
Reverse Leakage Current	I_R	V _{RWM} =±5.0V			100	nA
Clamping Voltage	Vc	I _{PP} =1.0A ,tp=8/20us			8.5	V
Clamping Voltage	Vc	I _{PP} =8.0A ,tp=8/20us			11	V
Junction Capacitance	С	V _R =0V, f =1MHz		19		pF